Docket No.: P2001,0520

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : BERTHOLD HAHN ET AL.

Filed : CONCURRENTLY HEREWITH

Title : METHOD FOR FABRICATING A LIGHT-EMITTING DEVICE

BASED ON A GALLIUM NITRIDE-BASED COMPOUND

SEMICONDUCTOR, AND LIGHT-EMITTING DEVICE BASED

ON A GALLIUM NITRIDE-BASED COMPOUND

SEMICONDUCTOR

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

U.S. Patent No. 6,015,979 (Sugiura et al.), dated January 18, 2000;

European Patent Application EP 0 732 754 A2 (Koike et al.), dated September 18, 1996:

European Patent Application EP 0 599 224 B1 and A1 (Nakamura et al.), dated June 1, 1994;

European Patent Application EP 0 993 048 A2 (Ishida et al.), dated April 12, 2000;

Kim, I.-H. et al.: "Formation of V-Shaped Pits in InGaN/GaN Multiquantum Wells and Bulk InGaN Films", Applied Physics Letters, Vol. 73, No. 12, September 21, 1998, pp. 1634-1636;

Chen, Y. et al.: "Pit Formation in GalnN Quantum Wells", Applied Physics Letters, Vol. 72, No. 6, February 9, 1998, pp. 710-712;

Wu, X. H. et al.: "Dislocation Generation in GaN Heteroepitaxy", Journal of Crystal Growth, Elsevier Science B.V., 189/190, 1998, pp. 231-243;

Kawaguchi, Y. et al.: "The Formation of Crystalline Defects and Crystal Growth Mechanism in In_xGa_{1-x}N/GaN Heterostructure Grown by Metalorganic Vapor Phase Epitaxy", Journal of Crystal Growth, Elsevier Science B.V., 189/190, 1998, pp. 24-28;

Gallart, M. et al.: "CW and Time-Resolved Optical Spectroscopy of GaN Epilayers and GaN-AlGaN Quantum Wells Grown on A-Plane Sapphire", Phys.Stat.Sol., (b), 216, 365, 1999, pp. 365-369;

Keller, S. et al.: "Spiral Growth of InGaN Nanoscale Islands on GaN", Japanese Journal of Applied Physics, Vol. 37, Part 2, No. 4B, April 15, 1998, pp. L431-L434;

Hangleiter, A. et al.: "Optical Absorption and Excitation Spectroscopy on GalnN/GaN Double Heterostructures and Quantum Wells", Materials Science Forum, Trans Tech Publications, Switzerland, Vols. 267-268, 1998, pp. 1287-1290;

Im, J. S. et al.: "Reduction of Oscillator Strength due to Piezoelectric Fields in GaN/Al_xGa_{1-x}N Quantum Wells", The American Physical Society, Physical Review B, Vol. 57, No. 16, April 15, 1998, pp. R9435-R9438;

Nakamura, S. et al.: "High-Power InGaN Single-Quantum-Well-Structure Blue and Violet Light-Emitting Diodes", American Institute of Physics, Appl. Phys. Lett. 67, (13), September 25, 1995, pp. 1868-1870;

Mukai, T.: "InGaN-Based Blue Light-Emitting Diodes Grown on Epitaxially Laterally Overgrown GaN Substrates", Publication Board, Japanese Journal of Applied Physics, Vol. 37, Part 2, No. 7B, July 15, 1998, pp. L839-L841;

Lester, S. D. et al.: "High Dislocation Densities in High Efficiency GaN-Based Light-Emitting Diodes", American Institute of Physics, Appl. Phys. Lett., Vol. 66, No. 10, March 6, 1995, pp. 1249-1251;

International Search Report, dated October 25, 2002.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant. As per the Notice in 1273 OG 55 (August 5, 2003) no copies of any above-mentioned U.S. patents and U.S. patent application publications are submitted for any application filed after June 30, 2003.

Respectfully submitted,

For Applicants

WERNER H. STEMER REG. NO. 34.956

Date: January 20, 2004

Lerner and Greenberg, P.A. Post Office Box 2480 Hollywood, FL 33022-2480

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FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE				Attorney Docket No.: P2001,0520 Appl. No.:				
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	Kim, IH. et al.: "Formation of V-Shaped Pits in InGaN/GaN Multiquantum Wells and Bulk InGaN Films", Applied Physics Letters, Vol. 73, No. 12, September 21, 1998, pp. 1634-1636							
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		Crystal Growth, Els	sevier Scient	Generation in GaN Fence B.V., 189/190, 1	1998, pp. 2	231-243				
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		Gallart, M. et al.: "CW and Time-Resolved Optical Spectroscopy of GaN Epilayers and GaN-AlGaN Quantum Wells Grown on A-Plane Sapphire", Phys.Stat.Sol., (b), 216, 365, 1999, pp. 365-369								
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